

REMARKS

The proposed amendments contained herein are to address matters of form only.
No new matter has been added. Accordingly, the Examiner is requested to enter this preliminary amendment.

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Respectfully submitted,

By 

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Version with Markings to Show Changes Made

IN THE SPECIFICATION:

Please amend paragraph 0088 as follows:

During the sleep mode, the overshoot preventive circuit 63 raises the voltage V_o to the level of the power source voltage V_{DD} by making the gate voltage of the P-MOS transistor 41 low to turn on the P-MOS transistor 41 when the detected current is smaller than a predetermined value $[I] \alpha$ (e.g., 1A). When the detected current is greater than the predetermined value $[I] \alpha$ (e.g., 1A), the overshoot preventive circuit 63 continuously raises the gate voltage of the P-MOS transistor 41 in response to the detected current so that the current supplied from the P-MOS transistor 41 is successively reduced to the level smaller than the predetermined value $[I] \alpha$ (e.g., 1A).